

## N-Channel 100-V (D-S) MOSFET

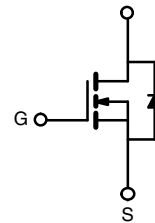
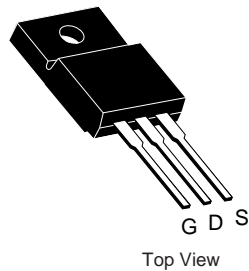
| PRODUCT SUMMARY |                           |           |
|-----------------|---------------------------|-----------|
| $V_{DS}$ (V)    | $R_{DS(on)}$ ( $\Omega$ ) | $I_D$ (A) |
| 100             | 0.0085 at $V_{GS} = 10$ V | 90        |
|                 | 0.0100 at $V_{GS} = 6$ V  | 85        |

### FEATURES

- TrenchFET<sup>®</sup> Power MOSFET
- 175 °C Maximum Junction Temperature
- Compliant to RoHS Directive 2002/95/EC



TO-220 FULLPAK



N-Channel MOSFET

| ABSOLUTE MAXIMUM RATINGS $T_A = 25$ °C, unless otherwise noted |                |                         |                 |   |
|--|----------------|-------------------------|-----------------|---|
| Parameter  | Symbol         | Limit                   | Unit            |   |
| Drain-Source Voltage   | $V_{DS}$       | 100                     | V               |   |
| Gate-Source Voltage  | $V_{GS}$       | $\pm 20$                |                 |   |
| Continuous Drain Current ( $T_J = 150$ °C)                     | $I_D$          | $T_C = 25$ °C           | 90              | A |
|  |                | $T_C = 125$ °C          | 70 <sup>a</sup> |   |
| Pulsed Drain Current   | $I_{DM}$       | 287                     |                 |   |
| Avalanche Current  | $I_{AS}$       | 75                      |                 |   |
| Single Pulse Avalanche Energy <sup>b</sup>                     | $E_{AS}$       | 280                     | mJ              |   |
| Maximum Power Dissipation <sup>b</sup>                         | $P_D$          | $T_C = 25$ °C (TO-220F) | 56              | W |
|  |                | $T_A = 25$ °C (TO-220F) | 3.75            |   |
| Operating Junction and Storage Temperature Range               | $T_J, T_{stg}$ | - 55 to 175             | °C              |   |

| THERMAL RESISTANCE RATINGS |            |                                 |      |      |
|----------------------------|------------|---------------------------------|------|------|
| Parameter                  | Symbol     | Limit                           | Unit |      |
| Junction-to-Ambient        | $R_{thJA}$ | PCB Mount (TO-220) <sup>d</sup> | 40   | °C/W |
|                            |            | Free Air (TO-220)               | 62.5 |      |
| Junction-to-Case           | $R_{thJC}$ | 0.6                             |      |      |

Notes:

- Pulse test; pulse width  $\leq 300$   $\mu$ s, duty cycle  $\leq 2$  %.
- Guaranteed by design, not subject to production testing.
- Independent of operating temperature.

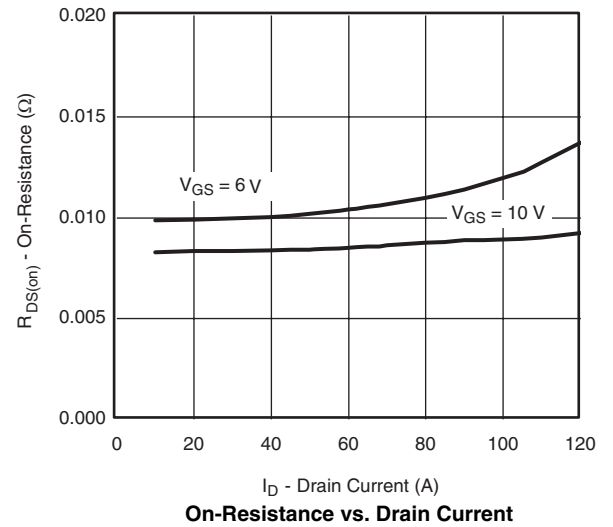
| <b>SPECIFICATIONS</b> $T_J = 25\text{ }^\circ\text{C}$ , unless otherwise noted                     |               |  |      |        |           |               |
|---|---------------|--|------|--------|-----------|---------------|
| Parameter   | Symbol        | Test Conditions  | Min. | Typ.   | Max.      | Unit          |
| <b>Static</b>   |               |  |      |        |           |               |
| Drain-Source Breakdown Voltage  | $V_{DS}$      | $V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$  | 100  |        |           | V             |
| Gate-Threshold Voltage  | $V_{GS(th)}$  | $V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$  | 1    |        | 3         |               |
| Gate-Body Leakage   | $I_{GSS}$     | $V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$  |      |        | $\pm 100$ | nA            |
| Zero Gate Voltage Drain Current   | $I_{DSS}$     | $V_{DS} = 100\text{ V}, V_{GS} = 0\text{ V}$   |      |        | 1         | $\mu\text{A}$ |
|   |               | $V_{DS} = 100\text{ V}, V_{GS} = 0\text{ V}, T_J = 125\text{ }^\circ\text{C}$  |      |        | 50        |               |
|   |               | $V_{DS} = 100\text{ V}, V_{GS} = 0\text{ V}, T_J = 175\text{ }^\circ\text{C}$  |      |        | 250       |               |
| On-State Drain Current <sup>a</sup>   | $I_{D(on)}$   | $V_{DS} \geq 5\text{ V}, V_{GS} = 10\text{ V}$   | 120  |        |           | A             |
| Drain-Source On-State Resistance <sup>a</sup>   | $R_{DS(on)}$  | $V_{GS} = 10\text{ V}, I_D = 30\text{ A}$  |      | 0.0095 |           | $\Omega$      |
|   |               | $V_{GS} = 6\text{ V}, I_D = 20\text{ A}$   |      | 0.0100 |           |               |
|   |               | $V_{GS} = 10\text{ V}, I_D = 30\text{ A}, T_J = 125\text{ }^\circ\text{C}$   |      | 0.0160 |           |               |
|   |               | $V_{GS} = 10\text{ V}, I_D = 30\text{ A}, T_J = 175\text{ }^\circ\text{C}$   |      | 0.0210 |           |               |
| Forward Transconductance <sup>a</sup>   | $g_{fs}$      | $V_{DS} = 15\text{ V}, I_D = 30\text{ A}$  | 25   |        |           | S             |
| <b>Dynamic<sup>b</sup></b>  |               |  |      |        |           |               |
| Input Capacitance   | $C_{iss}$     | $V_{GS} = 0\text{ V}, V_{DS} = 25\text{ V}, f = 1\text{ MHz}$  |      | 6550   |           | pF            |
| Output Capacitance  | $C_{oss}$     |  |      | 665    |           |               |
| Reverse Transfer Capacitance  | $C_{rss}$     |  |      | 265    |           |               |
| Total Gate Charge <sup>c</sup>  | $Q_g$         | $V_{DS} = 50\text{ V}, V_{GS} = 10\text{ V}, I_D = 85\text{ A}$  |      | 105    |           | nC            |
| Gate-Source Charge <sup>c</sup>   | $Q_{gs}$      |  |      | 17     |           |               |
| Gate-Drain Charge <sup>c</sup>  | $Q_{gd}$      |  |      | 23     |           |               |
| Turn-On Delay Time <sup>c</sup>   | $t_{d(on)}$   | $V_{DD} = 50\text{ V}, R_L = 0.6\text{ }\Omega$<br>$I_D \cong 85\text{ A}, V_{GEN} = 10\text{ V}, R_g = 2.5\text{ }\Omega$ |      | 12     | 25        | ns            |
| Rise Time <sup>c</sup>  | $t_r$         |  |      | 90     | 135       |               |
| Turn-Off Delay Time <sup>c</sup>  | $t_{d(off)}$  |  |      | 55     | 85        |               |
| Fall Time <sup>c</sup>  | $t_f$         |  |      | 130    | 195       |               |
| <b>Source-Drain Diode Ratings and Characteristics</b> $T_C = 25\text{ }^\circ\text{C}$ <sup>b</sup> |               |  |      |        |           |               |
| Continuous Current  | $I_S$         |  |      | 90     |           | A             |
| Pulsed Current  | $I_{SM}$      |  |      | 240    |           |               |
| Forward Voltage <sup>a</sup>  | $V_{SD}$      | $I_F = 85\text{ A}, V_{GS} = 0\text{ V}$   |      | 1.0    | 1.5       | V             |
| Reverse Recovery Time   | $t_{rr}$      | $I_F = 50\text{ A}, di/dt = 100\text{ A}/\mu\text{s}$  |      | 85     | 140       | ns            |
| Peak Reverse Recovery Current   | $I_{RM(REC)}$ |  |      | 4.5    | 7         | A             |
| Reverse Recovery Charge   | $Q_{rr}$      |  |      | 0.17   | 0.35      | $\mu\text{C}$ |

## Notes:

- Pulse test; pulse width  $\leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$ .
- Guaranteed by design, not subject to production testing.
- Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

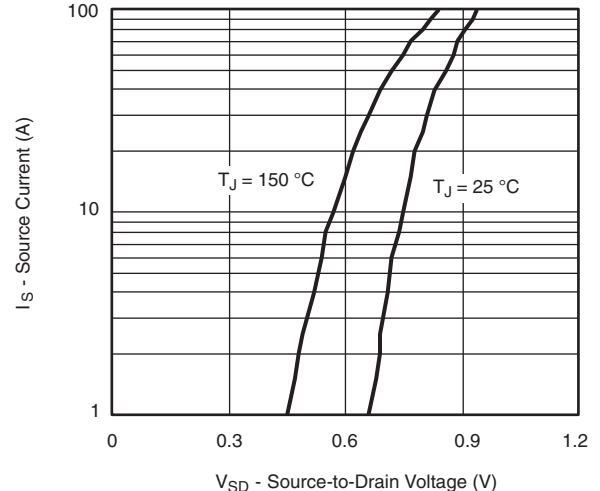
**TYPICAL CHARACTERISTICS**  $T_A = 25\text{ }^\circ\text{C}$ , unless otherwise noted



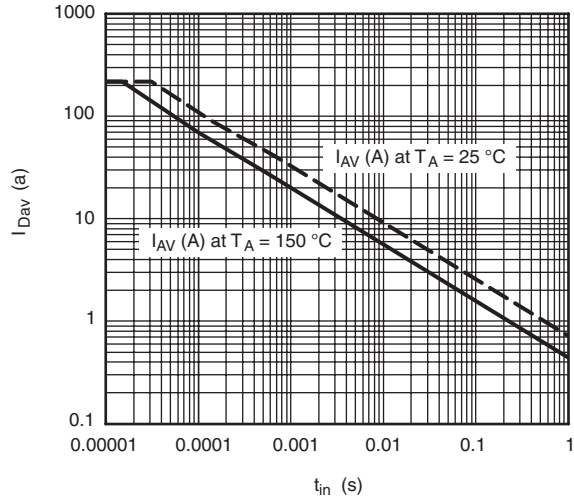
**TYPICAL CHARACTERISTICS**  $T_A = 25\text{ }^\circ\text{C}$ , unless otherwise noted



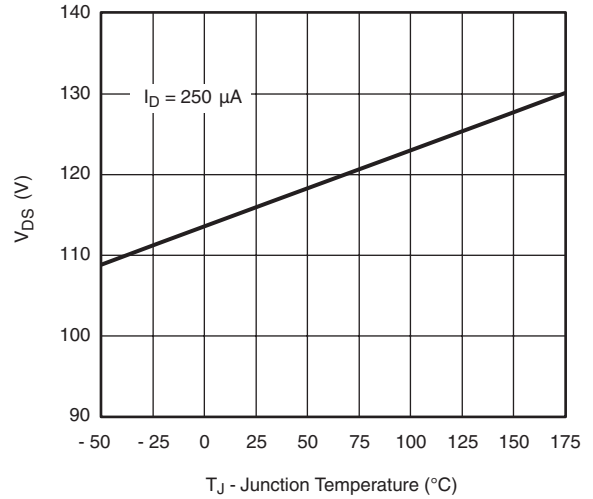
**On-Resistance vs. Junction Temperature**



**Source-Drain Diode Forward Voltage**



**Avalanche Current vs. Time**



**T<sub>J</sub> - Drain-Source Breakdown vs. Junction-Temperature**

**THERMAL RATINGS**



**Maximum Avalanche and Drain Current vs. Case Temperature**

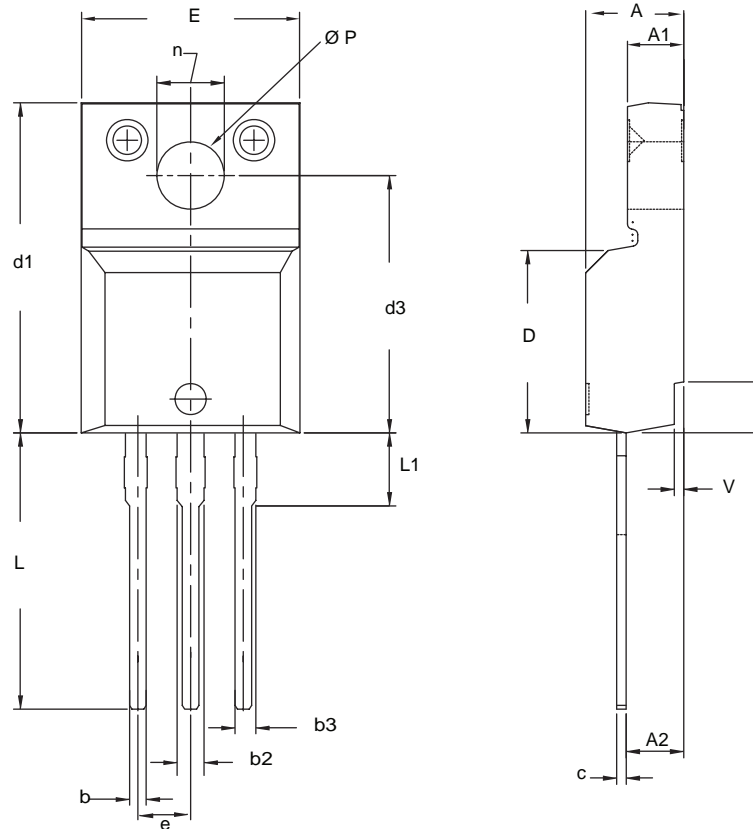


**Safe Operating Area**  
\*  $V_{GS} >$  minimum  $V_{GS}$  at which  $R_{DS(on)}$  is specified



**Normalized Thermal Transient Impedance, Junction-to-Case**

**TO-220 FULLPAK (HIGH VOLTAGE)**



| DIM.            | MILLIMETERS |        | INCHES    |       |
|-----------------|-------------|--------|-----------|-------|
|                 | MIN.        | MAX.   | MIN.      | MAX.  |
| A               | 4.570       | 4.830  | 0.180     | 0.190 |
| A1              | 2.570       | 2.830  | 0.101     | 0.111 |
| A2              | 2.510       | 2.850  | 0.099     | 0.112 |
| b               | 0.622       | 0.890  | 0.024     | 0.035 |
| b2              | 1.229       | 1.400  | 0.048     | 0.055 |
| b3              | 1.229       | 1.400  | 0.048     | 0.055 |
| c               | 0.440       | 0.629  | 0.017     | 0.025 |
| D               | 8.650       | 9.800  | 0.341     | 0.386 |
| d1              | 15.88       | 16.120 | 0.622     | 0.635 |
| d3              | 12.300      | 12.920 | 0.484     | 0.509 |
| E               | 10.360      | 10.630 | 0.408     | 0.419 |
| e               | 2.54 BSC    |        | 0.100 BSC |       |
| L               | 13.200      | 13.730 | 0.520     | 0.541 |
| L1              | 3.100       | 3.500  | 0.122     | 0.138 |
| n               | 6.050       | 6.150  | 0.238     | 0.242 |
| $\varnothing P$ | 3.050       | 3.450  | 0.120     | 0.136 |
| u               | 2.400       | 2.500  | 0.094     | 0.098 |
| v               | 0.400       | 0.500  | 0.016     | 0.020 |

ECN: X09-0126-Rev. B, 26-Oct-09  
DWG: 5972

**Notes**

1. To be used only for process drawing.
2. These dimensions apply to all TO-220, FULLPAK leadframe versions 3 leads.
3. All critical dimensions should C meet  $C_{pk} > 1.33$ .
4. All dimensions include burrs and plating thickness.
5. No chipping or package damage.

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